Standard Products UT200SpWPHY01 SpaceWire Physical Layer Transceiver

Datasheet

August, 2006



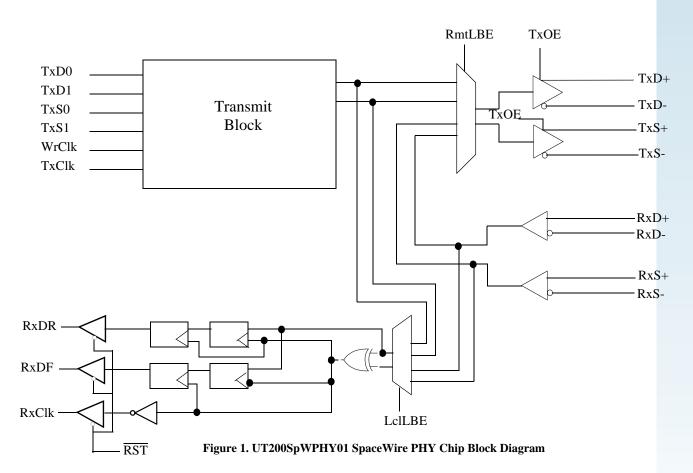
FEATURES

- □ 2-bit Serializer/Deserializer (SerDes) functionality
- □ LVDS physical layer
- Data rates to 200 Mbits/sec
- □ Data/Strobe transmit skew <500pS
- □ 3.3V power supply
- □ Cold spare on LVDS pins
- Radiation-hardened design; total dose irradiation testing to MIL-STD-883 Method 1019
 - Total-dose: 100 krad(Si)
 - Latchup immune (LET > 110 MeV-cm²/mg)
- □ ESD rating Class 1
- Deckaged in a 28-pin flatpack
- □ Standard Microcircuit Drawing 5962-06232
 - QML Q and V compliant part

INTRODUCTION

Aeroflex Colorado Springs' UT200SpWPHY01 Physical Layer Transceiver (PHY) is designed to handle the critical timing issues associated with the SpaceWire Data/Strobe Encoding scheme.

The receiver operates on both edges of the recovered RxClk and provides data on the digital outputs in bit pairs. The transmitter operation is the reverse of the receiver. Bit pairs of data and strobe are written into the device on the WrClk signal and the PHY serializes data and strobe onto the LVDS bus using the TxClk signal. The advantages of this SerDes functionality is the interfacing FPGA or ASIC can run at reduced clock rate with high-speed clock not requiring a stringent phase relationship.



APPLICATIONS INFORMATION

Aeroflex Colorado Springs' UT200SpWPHY01 SpaceWire Physical Layer Transceiver is designed to maximize the speed of SpaceWire links implemented in Field Programmable Gate Arrays. The UT200SpWPHY01 is designed to handle the critical timing issues associated with the SpaceWire data/strobe encoding scheme.

Receiver Fail-Safe

The UT200SpWPHY01 SpaceWire Physical Layer Transceiver is a high gain, high speed device that amplifies a small differential signal (20mV) to TTL logic levels. Due to the high gain and tight threshold of the receiver, care should be taken to prevent noise from appearing as a valid signal.

The receiver's internal fail-safe circuitry is designed to source/ sink a small amount of current, providing fail-safe protection (a stable known state of HIGH output voltage) for floating, terminated or shorted receiver inputs.

1. **Open Input Pins.** If an application requires an unused channel, the inputs should be left OPEN. Do not tie unused receiver inputs to ground or any other voltages. The input is biased by internal high value pull up and pull down resistors to set the output to a HIGH state. This internal circuitry will guarantee a HIGH, stable output state for open inputs.

2. **Terminated Input**. If the driver is disconnected (cable unplugged), or if the driver is in a three-state or power-off condition, the receiver output will again be in a HIGH state, even with the end of cable 100Ω termination resistor across the input pins. The unplugged cable can become a floating antenna which can pick up noise. If the cable picks up more than 10mV of differential noise, the receiver may see the noise as a valid signal and switch. To insure that any noise is seen as common-mode and not differential, a balanced interconnect should be used. Twisted pair cable offers better balance than flat ribbon cable.

Shorted Inputs. If a fault condition occurs that shorts the receiver inputs together, thus resulting in a 0V differential input voltage, the receiver output remains in a HIGH state. Shorted input fail-safe is not supported across the common-mode range of the device (V_{SS} to 2.4V). It is only supported with inputs shorted and no external common-mode voltage applied.

TxOE	RST	LclLBE	RmtLBE	Tx Outputs	Rx Outputs
0	0	Х	Х	Hi-Z	Hi-Z
1	1	0	0	CMOS Tx Inputs	LVDS Rx Inputs
0	1	0	Х	Hi-Z	LVDS Rx Inputs
0	1	1	Х	Hi-Z	CMOS Tx Inputs
1	0	Х	0	0	Hi-Z
1	0	X	1	LVDS Rx Inputs	Hi-Z
1	1	0	1	LVDS Rx Inputs	LVDS Rx Inputs
1	1	1	0	CMOS Tx Inputs	CMOS Tx Inputs
1	1	1	1	LVDS Rx Inputs	CMOS Tx Inputs

Table 1: SpaceWire Physical Layer Transceiver Device Operation Truth Table

RADIATION

Parameter	Limit	Units
Total Ionizing Dose (TID)	>3E5 and 1E6	rads(Si)
Single Event Latchup (SEL) ^{1, 2}	>109	MeV-cm ² /mg
SEU Saturated Cross-Section (σ_{sat})	1.0E-8	cm ² /device
Onset Single Event Upset (SEU) LET Threshold ³	109	MeV-cm ² /mg
Neutron Fluence	1.0E14	n/cm ²
Dose Rate Upset	TBD	rads(Si)/sec
Dose Rate Survivability	TBD	rads(Si)/sec

Notes:

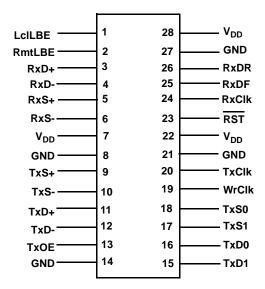
1. The UT200SpW02 are latchup immune to particle LETs >109 MeV-cm²/mg. 2. Worst case temperature and voltage of $T_C = +125^{\circ}C$, $V_{DD} = 3.6V$, $V_{DD}Q1/Q3/Q4 = 3.6V$ for SEL.

3. Worst case temperature and voltage of $T_C = +25^{\circ}C$, $V_{DD} = 3.0V$, $V_{DD}Q1/Q3/Q4 = 3.0V$ for SEU.

4.Adams 90% worst case particle environment, Geosynchronous orbit, 100mils of Aluminum shielding.

28-pin Flatpack Pin Description Pin Name Pin Pin Type Description				
1 111 1 (unite	Number	I III I,pc		
LclLBE	1	LVCMOS Input ¹	Local Loopback Enable 0: No loopback, received data comes from LVDS Rx inputs (RxD+,) 1: Local loopback, received data comes from LVCMOS Tx inputs (TxD0,)	
RmtLBE	2	LVCMOS Input ¹	Remote Loopback Enable0: No loopback, Transmit LVDS data comes from the LVCMOS Tx inputs (TxD0,)1. Remote Loopback, Transmit LVDS data comes from LVDS Rx inputs.	
RxD+	3	LVDS Input	LVDS Rx differential positive Data input	
RxD-	4	LVDS Input	LVDS Rx differential negative Data input	
RxS+	5	LVDS Input	LVDS Rx differential positive Strobe input	
RxS-	6	LVDS Input	LVDS Rx differential negative Strobe input	
V _{DD}	7, 22, 28		VDD 3.3V power supply	
GND	8,14,21,27		Vss 0V	
TxS+	9	LVDS Output	LVDS Tx differential positive Strobe output	
TxS-	10	LVDS Output	LVDS Tx differential negative Strobe output	
TxD+	11	LVDS Output	LVDS Tx differential positive Data output	
TxD-	12	LVDS Output	LVDS Tx differential negative Data output	
TxOE	13	LVCMOS Input ¹	TxOE=High: Enables LVDS transmit TxOE=Low: Tri-states LVDS transmit	
RxDR	26	LVCMOS Output	Receiver rising edge (even) bit output (See Figure 7)	
RxDF	25	LVCMOS Output	Receiver falling edge (odd) bit output (See Figure 7)	
RxClk	24	LVCMOS Output	Receiver clock output	
RST	23	LVCMOS Input ¹	RST must remain low for 3 clock cycles before transitioning high, and must transition high 3 clock cycles before valid data.	
TxClk	20	LVCMOS Input ¹	Clock input to transmitter used to clock LVDS output. Any phase relationship is allowed between TxClk & WrClk but both must come from the same clock sourc and TxClk must be twice the frequency of the WrClk.	
WrClk	19	LVCMOS Input ¹	Transmitter input data Clock used to clock CMOS input to transmitter. Any phase relationship is allowed betwee TxClk & WrClk but both must come from the same cloc source and WrClk must 1/2 of TxClk.	
TxS0	18	LVCMOS Input	First (even) bit of 2bit parallel strobe input to transmitt	
TxS1	17	LVCMOS Input	Second (odd) bit of 2bit parallel strobe input to transmitter	
TxD0	16	LVCMOS Input	First, even bit of 2bit parallel data input to transmitter	
TxD1	15	LVCMOS Input	Second, odd bit of 2bit parallel data input to transmitt	

PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS¹

(Referenced to V_{SS})

SYMBOL	PARAMETER	LIMITS
V _{DD}	DC supply voltage	-0.3 to 4.0V
V _{I/O}	Voltage on any pin during operation	-0.3 to (V _{DD} + 0.3V)
	Voltage on any LVDS pin during cold spare ²	3 to 4.0V
T _{STG}	Storage temperature	-65 to +150°C
P _D	Maximum power dissipation	432 mW
Θ _{JC}	Thermal resistance, junction-to-case ³	10°C/W
II	DC input current	±10mA

Notes:

1. Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions beyond limits indicated in the operational sections of this specification is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability and performance.

LVCMOS pins are not cold spare.
 Test per MIL-STD-883, Method 1012.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS
V _{DD}	DC Supply Voltage	3.0V to 3.6V
VIN	DC input voltage	0V to V _{DD}

DC ELECTRICAL CHARACTERISTICS¹

 $(V_{DD} = 3.3V \pm 0.3V; -55^{\circ}C < T_C < +125^{\circ}C)$

SYMBOL	PARAMETER	CONDITION	MIN	MAX	UNIT
V _{IH}	High-level input voltage (CMOS)		2.0		V
V _{IL}	Low-level input voltage (CMOS)			0.8	V
V _{OL}	Low-level output voltage (LVCMOS)	IOL = 12mA		0.4	V
V _{OH}	High-level output voltage (LVCMOS)	IOH = -12mA	2.4		V
I _{INLVDS}	Input leakage current	$V_{IN} = V_{DD}$ or GND, $V_{DD} = 3.6V$	-20	+20	μΑ
I _{INCMOS}	Input leakage current	$V_{IN} = V_{DD}$ or GND, $V_{DD} = 3.6V$	-10	+10	μΑ
I _{CS}	Cold Spare Leakage Current	V_{IN} =3.6V, V_{DD} = V_{SS} = 0V	-20	+20	μΑ
V _{TH}	Differential Input High Threshold	VCM = +1.2V		+100	mV
V _{TL}	Differential Input Low Threshold	VCM = +1.2V	-100		mV
V _{OD}	Differential Output Voltage	$R_L = 100\Omega$	250	400	mV
ΔV_{OD}	Change in Magnitude of V _{OD} for Complementary Output States	$R_L = 100\Omega$		35	mV
V _{OS}	Offset Voltage	$R_{L} = 100\Omega, \left(Vos = \frac{Voh + Vol}{2}\right)$	1.125	1.450	V
ΔV_{OS}	Change in Magnitude of V _{OS} for Complementary Output States	$R_L = 100\Omega$		25	mV
I _{OZ}	LVDS Output Three-State Current	$TxOE = Gnd$ $V_{OUT} = 0V \text{ or } V_{DD}, V_{DD} = 3.6V$	-10	+10	μΑ
I _{CCL}	Loaded supply current, drivers enabled	$\begin{split} R_L &= 50\Omega \text{ all channels, running in full} \\ duplex \\ V_{IN} &= V_{DD} \text{ or } V_{SS}(\text{all inputs}) \\ C_L &= 37 \text{pF, F} = 200 \text{MHz} \end{split}$		120	mA
I _{CCZ}	Loaded supply current, drivers disabled	$D_{IN} = V_{DD}$ or V_{SS} Clock and Data not toggling		10	mA
I _{CCI}	Supply current, data toggling, clocks running, device in standby	Clock @ 200 Mhz, $TxOE = 0$ Data @ 200 Mbits/sec, $\overline{RST} = 0$		25	mA
C_{IN}^{2}	LVCMOS input capacitance	f = 1MHz @ 0V		7	pF
C _{OUT} ²	LVCMOS output capacitance	f = 1MHz @ 0V		15	pF
C _{INLVDS} ²	LVDS input capacitance	f = 1MHz @ 0V		6	pF
C _{OUTLVDS} ²	LVDS output capacitance	f = 1MHz @ 0V		7	pF

Notes:

Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground except differential voltages.
 Capacitance is measured for initial qualification and when design changes may affect the input/output capacitance. Capacitance is measured between the designated terminal and V_{SS} at a frequency of 1MHz and a signal amplitude of 50mV maximum.

AC SWITCHING CHARACTERISTICS

 $(V_{DD} = +3.3V \pm 0.3V, T_A = -55 \text{ °C to } +125 \text{ °C})$

SYMBOL	PARAMETER	MIN	MAX	UNIT
t _{CDLH}	TxClk to differential Data output low to high prop delay $R_L=50$, $C_L=37pF$ (figure 2)	2	4	ns
t _{CDHL}	TxClk to differential Data output high to low prop delay $R_L=50$, $C_L=37pF$ (figure 2)	2	4	ns
t _{CSLH}	TxClk to differential Strobe output low to high prop delay $R_L=50$, $C_L=37pF$ (figure 2)	2	4	ns
t _{CSHL}	TxClk to differential Strobe output high to low prop delay $R_L=50$, $C_L=37pF$ (figure 2)	2	4	ns
t _{DCS}	Differential Channel Skew		0.4	ns
t _{CCS} ¹	Channel to Channel Skew		0.5	ns
t _{TLH} ²	Rise time LVDS Driver (figure 2) $R_L=100$, $C_L=37pF$		1.5	ns
t _{THL} ²	Fall time LVDS Driver (figure 2) R_L =100, C_L = 37pF		1.5	ns
t _{OEHZ}	Output Enable Low to Data or Strobe High to Z (figure 3, 4) $R_L = 50$, $C_L = 37 pF$		5	ns
t _{OELZ}	Output Enable Low to Data or Strobe Low to Z (figure 3, 4) $R_L = 50$, $C_L = 37 pF$		5.0	ns
t _{OEZH}	Output Enable High to Data or Strobe Z to High (figure 3, 4) $R_L = 50$, $C_L = 37 pF$		5	ns
t _{OEZL}	Output Enable High to Data or Strobe Z to Low (figure 3, 4) $R_L = 50$, $C_L = 37 pF$		5.0	ns
t _{SETUP TX}	Minimum required setup of Data or Strobe with respect to WrClk (figure 6)	2		ns
t _{HOLD TX}	Minimum required hold of Data or Strobe with respect to WrClk (figure 6)	0		ns
t _{INRISE} ³	Maximum rise time into Data/Strobe inputs (0.8V to 2V)		14	% of bit width
t _{INFALL} ³	Maximum fall time into Data/Strobe inputs (0.8V to 2V)		14	% of bit width
t _{DRST}	Minimum number of full clock cycles (WrClk) between rising edge of $\overline{\text{RST}}$ and rising edge of first valid data or strobe (TxDO, TxD1, TxS0, TxS1) (figure 5)	3		WrClk cycles
t _{CRST}	Minimum number of full clock cycles (WrClk) that \overline{RST} must remain low before \overline{RST} can transition high (figure 5)	3		WrClk cycles
t _{CO}	Delay between RxClk falling and data edge (figure 7)		1	ns
t _{RLZ}	Delay between $\overline{\text{RST}}$ going low and CMOS output tri-state (figure 7) R _L = 50, C _L = 37pF		5	ns
t _{RHV}	Delay between $\overline{\text{RST}}$ going high and CMOS output valid (figure 7) $R_L = 50$, $C_L = 37 pF$		5	ns
t _{RISE}	CMOS 20-80% Receiver output rise time (figure 8) $C_L = 37 pF$		1	ns
t _{FALL}	CMOS 20-80% Receiver output fall time (figure 8) $C_L = 37 pF$		1	ns
t_S^3	LVDS Rx input data to strobe separation (figure 9)	2.5		ns
TxClk _{PMIN}	Minimum Transmit Clock period		5	ns
WrClk _{PMIN}	Minimum Write Clock period		10	ns
t _{CPMIN}	Minimum High or Low Clock Pulse Width	2		ns

Notes:

Notes:
1. Includes differential skew
2. Guaranteed by characterization
3. Specified as a design guidelines only, not tested.
4. 2.5 ns of separation requires a R_{XOUT} Load of <= 10pF

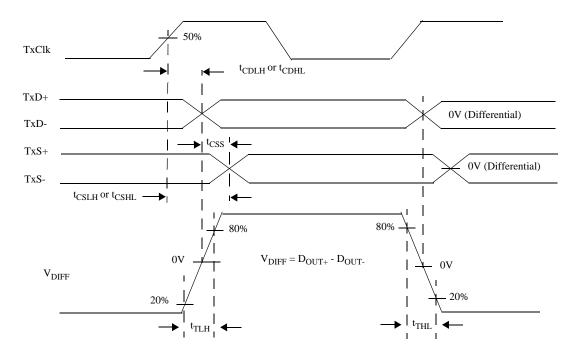


Figure 2. Driver Rise and Fall times and Channel Skew

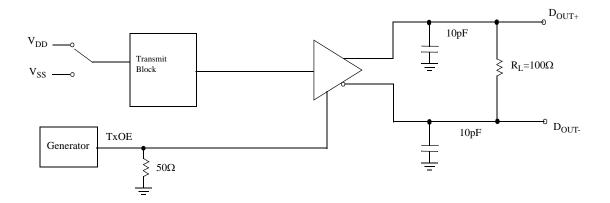


Figure 3. Driver Three-State Delay Time Test or Equivalent Circuit

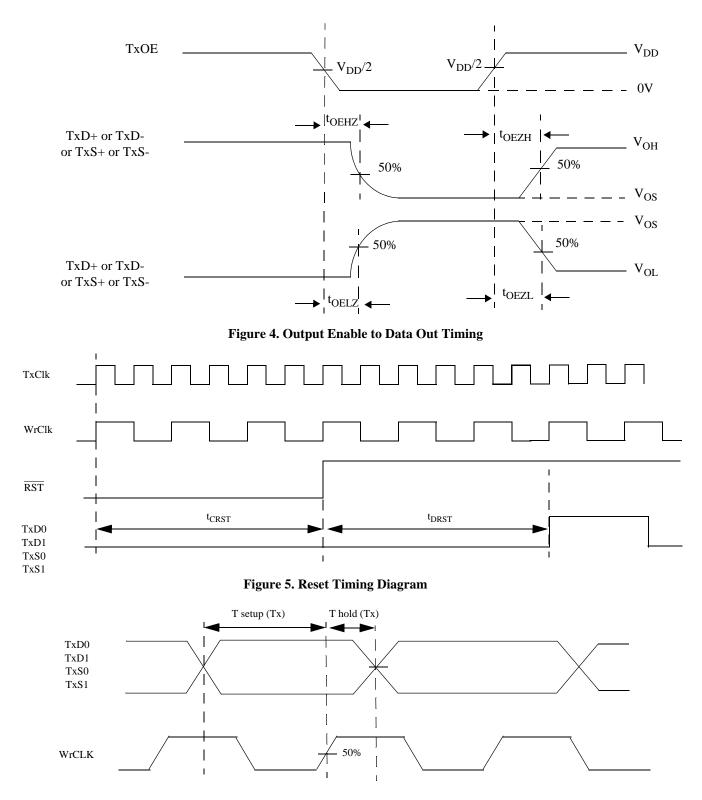


Figure 6. Transmitter Input Timing Diagram

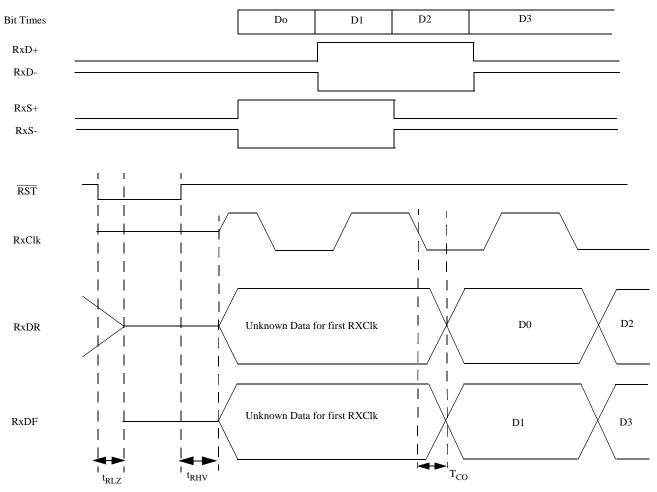


Figure 7. Receiver Output Timing Diagram

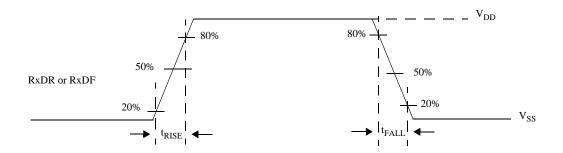


Figure 8. Receiver Output Rise and Fall Times Waveform

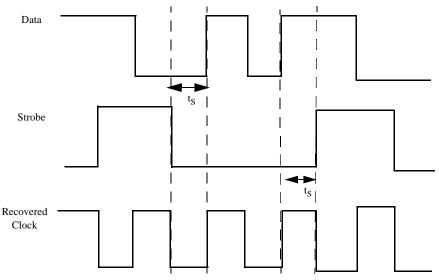
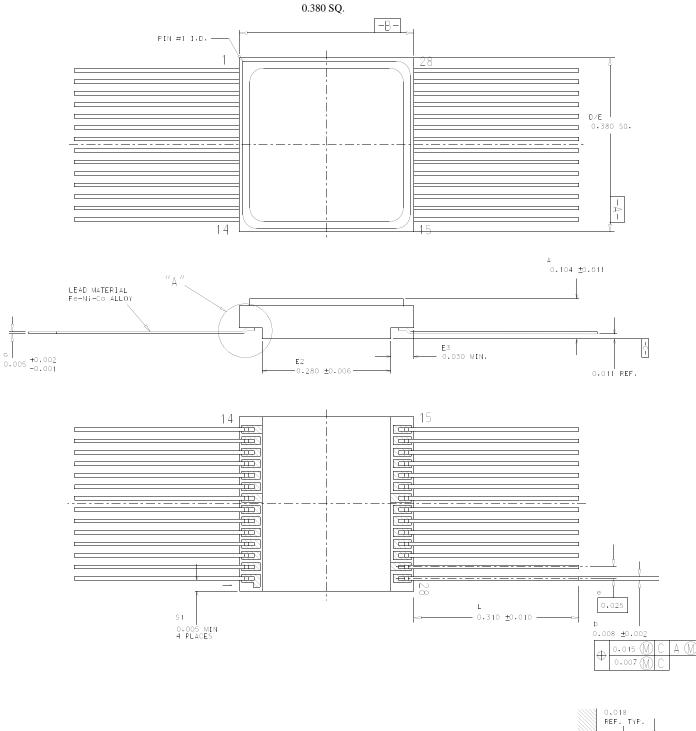


Figure 9. Data/Strobe Separation

PACKAGING





1. All exposed metallized areas are gold plated over electrically plated nickel per MIL-PRF-38535.

2. The lid is electrically connected to V_{SS} .

3. Lead finishes are in accordance with MIL-PRF-38535.

4. Dimension symbology is in accordance with MIL-PRF-38535.

5. Lead position and coplanarity are not measured.

6. ID mark symbol is vendor option: no alphanumerics.

Figure 10. 28-pin Flatpack

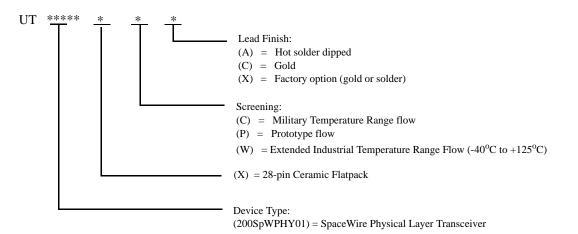
0.033 REF. TYP.

0.008 ±0.006

DETAIL A

ORDERING INFORMATION

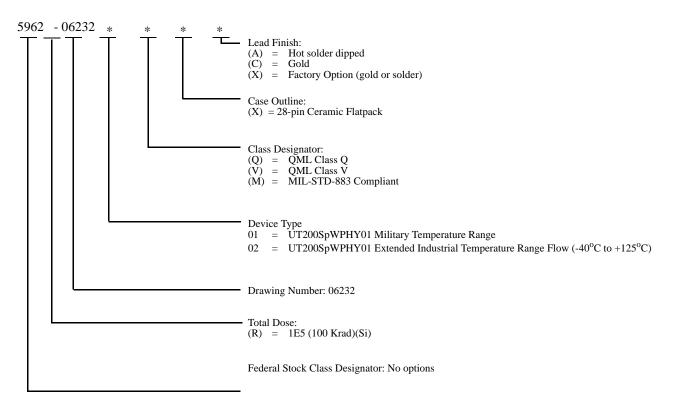
UT200SpWPHY01: SpaceWire Physical Layer Transceiver



Notes:
1. Lead finish (A,C, or X) must be specified.
2. If an "X" is specified when ordering, then the part marking will match the lead finish and will be either "A" (solder) or "C" (gold).

3. Prototype flow per Aeroflex Manufacturing Flows Document. Tested at 25°C only. Lead finish is GOLD ONLY. Radiation neither tested nor guaranteed. Military Temperature Range flow per Aeroflex Manufacturing Flows Document. Devices are tested at -55°C, room temp, and 125°C. Radiation neither tested nor guaranteed.

UT200SpWPHY01: SMD



Notes:

1.Lead finish (A,C, or X) must be specified.

2.If an "X" is specified when ordering, part marking will match the lead finish and will be either "A" (solder) or "C" (gold).

3. Total dose radiation must be specified when ordering. QML Q and QML V not available without radiation hardening.

COLORADO

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Our passion for performance is defined by three attributes represented by these three icons: solution-minded, performance-driven and customer-focused

